

# DATA SHEET

## **CGY2030M** **DECT 500 mW power amplifier**

Product specification  
Supersedes data of 1996 Jul 12  
File under Integrated Circuits, IC17

1997 Jan 17

# DECT 500 mW power amplifier

# CGY2030M

### FEATURES

- Power Amplifier (PA) overall efficiency 40%
- 27 dB gain
- 0 dBm input power
- Operation possible without negative supply
- Wide operating temperature range -30 to +85 °C
- SSOP16 package.

### GENERAL DESCRIPTION

The CGY2030M is a GaAs Monolithic Microwave Integrated Circuit (MMIC) power amplifier specifically designed to operate at 3.6 V battery supply. When power control is not required, it can be operated without negative supply voltage.

### APPLICATIONS

- 1.88 to 1.9 GHz transceivers for DECT applications
- 2 GHz transceivers (PHS, DCS).

### QUICK REFERENCE DATA

SYMBOL	PARAMETER <sup>(1)</sup>	MIN.	TYP.	MAX.	UNIT
V <sub>DD</sub>	positive supply voltage	-	3.2	-	V
I <sub>DD</sub>	positive peak supply current	-	400	-	mA
P <sub>o</sub>	output power	-	27	-	dBm
T <sub>amb</sub>	operating ambient temperature	-30	-	+85	°C

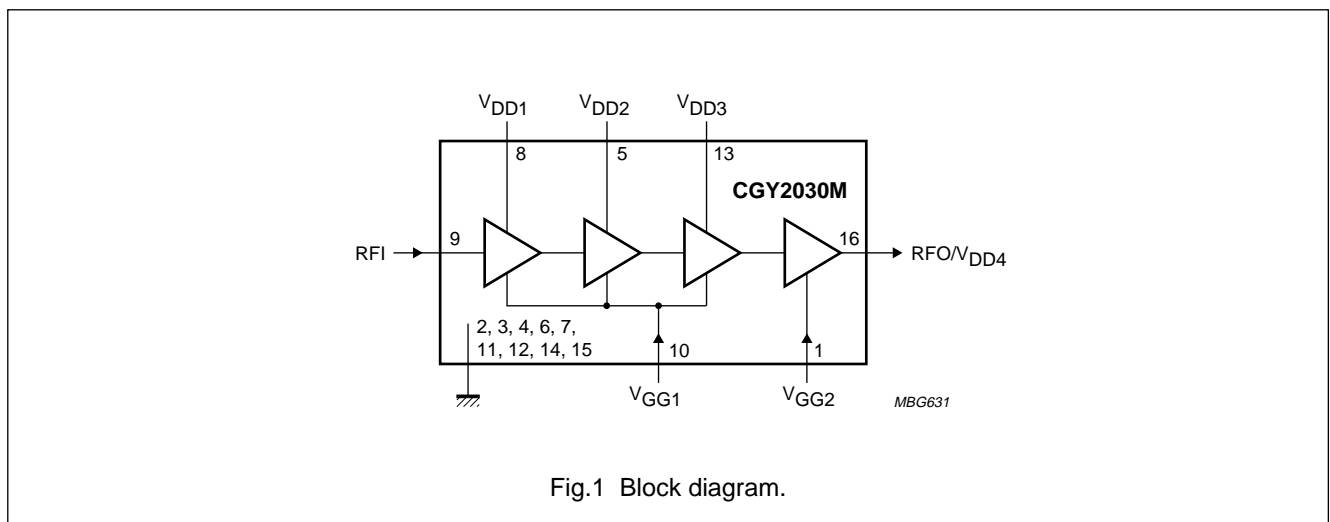
### Note

1. For conditions, see Chapters "AC characteristics" and "DC characteristics".

### ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
CGY2030M	SSOP16	plastic shrink small outline package; 16 leads; body width 4.4 mm	SOT369-1

### BLOCK DIAGRAM



DECT 500 mW power amplifier

CGY2030M

**PINNING**

SYMBOL	PIN	DESCRIPTION
V <sub>GG2</sub>	1	fourth stage negative gate supply voltage
GND	2 to 4	ground
V <sub>DD2</sub>	5	second stage supply voltage
GND	6 and 7	ground
V <sub>DD1</sub>	8	first stage supply voltage
RFI	9	PA input
V <sub>GG1</sub>	10	first second and third stages negative gate supply voltage
GND	11 and 12	ground
V <sub>DD3</sub>	13	third stage supply voltage
GND	14 and 15	ground
RFO/V <sub>DD4</sub>	16	PA output and fourth stage supply voltage

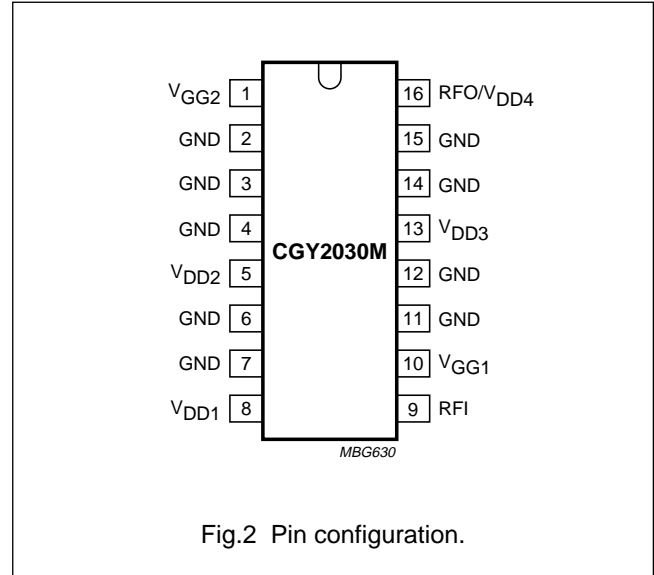


Fig.2 Pin configuration.

**FUNCTIONAL DESCRIPTION**

**Amplifier**

The CGY2030M is a 4-stage GaAs MESFET power amplifier capable of delivering 500 mW (typ.) at 1.9 GHz into a 50 Ω load. Each amplifier stage has an open-drain configuration. The drains have to be loaded externally by adequate reactive circuits which must also provide a DC path to the supply.

The amplifier can be switched off by means of an external PNP series switch connected between the battery and the amplifier drains. This switch can also be used to vary the actual supply voltage applied to the amplifier and hence, control the output power.

This device is specifically designed to work with a maximum duty factor of 25%.

**Biasing**

Two modes of operation are possible:

- Mode 1
- Mode 2.

**MODE 1**

In the first mode, the pins V<sub>GG1</sub> and V<sub>GG2</sub> are simply connected together to the ground via resistors (10 kΩ in the evaluation board; see Fig.4). The amplifier biases itself internally to a negative voltage by action of the incoming RF signal. In this mode, power control cannot be achieved by varying the amplifier supply voltage; therefore it is suitable only for applications where power control is not required such as DECT.

**MODE 2**

If a negative bias is available, a second mode of operation is possible, in which the amplifier is biased by providing adequate negative voltages at pins V<sub>GG1</sub> and V<sub>GG2</sub>. In this mode, the amplifier internal bias does not depend on the incoming RF level, nor on the drain voltage, so that power control is possible by variation of the supply voltage.

## DECT 500 mW power amplifier

CGY2030M

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{DD}$	operating supply voltage		–	–	5.2	V
$V_{DD} - V_{GG}$	voltage difference between supply voltage and gate bias voltage	no input signal	–	–	8	V
$T_{j(max)}$	maximum operating junction temperature		–	–	150	°C
$P_{tot}$	total power dissipation		–	–	400	mW
$T_{stg}$	IC storage temperature		–55	–	+125	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient in free air	145	K/W

**HANDLING**

Do not operate or store near strong electrostatic fields. Meets class 1 ESD test requirements [Human Body Model (HBM)], in accordance with "MIL STD 883C - method 3015".

**DC CHARACTERISTICS**

$V_{DD} = 3.2\text{ V}$ ;  $T_{amb} = 25\text{ °C}$ ; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Pins RFO/<math>V_{DD4}</math>, <math>V_{DD3}</math>, <math>V_{DD2}</math> and <math>V_{DD1}</math></b>						
$V_{DD}$	positive supply voltage		2.6	3.2	4.2	V
$I_{DD}$	positive peak supply current		–	400	500	mA
<b>Pins <math>V_{GG1}</math> and <math>V_{GG2}</math>; in mode 2</b>						
$V_{GG1}$	bias voltage for input stages	note 1	–	–1.2	–	V
$V_{GG2}$	bias voltage for output stage	note 1	–	–2.0	–	V
$I_{GG(tot)}$	total gate peak current	note 2	–1	–	+1	mA

**Notes**

1. Negative voltages  $V_{GG1}$  and  $V_{GG2}$  must be applied before supply voltage  $V_{DD}$ .
2. Due to non linear effects at high power levels, the gate current can be either negative or positive.

DECT 500 mW power amplifier

CGY2030M

AC CHARACTERISTICS

$V_{DD} = 3.2\text{ V}$ ;  $f_{RF} = 1900\text{ MHz}$ ;  $P_i = 0\text{ dBm}$ ;  $T_{amb} = 25\text{ }^\circ\text{C}$ ; duty factor  $\delta = 25\%$ ;  $50\text{ }\Omega$  impedance system; measured and guaranteed on CGY2030M evaluation board (see Fig.4).

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$P_i$	input power	note 1	-3	-	+5	dBm
$\delta$	duty factor		-	-	25	%
$f_{RF}$	operating frequency		-	1900	-	MHz
<b>Measured in mode 1; without negative biasing; <math>V_{GG1}</math> and <math>V_{GG2}</math> connected to ground</b>						
$P_o$	output power		26	27	28.5	dBm
$\eta$	efficiency		-	40	-	%
$P_{leak}$	RF leakage to output in power off state	$V_{DD} = 0\text{ V}$	-	-40	-	dBm
H2, H3	second and third harmonics level		-	-35	-	dBc
Stab	stability (spurious levels)	note 2	-	-60	-	dBc
<b>Measured in mode 2; with negative biasing at pins <math>V_{GG1}</math> and <math>V_{GG2}</math></b>						
$P_o$	output power		25.5	26.5	28	dBm
$\eta$	efficiency		-	35	-	%
$P_{leak}$	RF leakage to output in power off state	$V_{DD} = 0\text{ V}$	-	-50	-	dBm

Notes

1. Self biasing guaranteed in mode 1 at minimum input power (-3 dBm) and minimum supply voltage  $V_{DD}$  (2.6 V).
2. The device is adjusted to provide nominal value of load power into a  $50\text{ }\Omega$  load. The device is switched off and a 6 : 1 load replaces the  $50\text{ }\Omega$  load. The device is switched on and the phase of the 6 : 1 load is varied 360 electrical degrees during a 60 seconds test period.

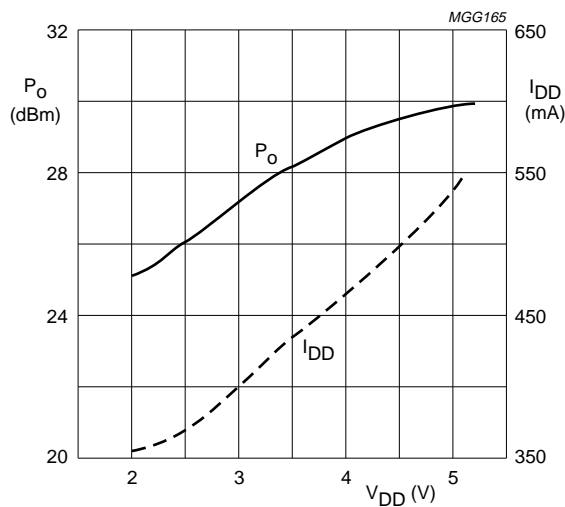


Fig.3 Typical power and current characteristics in mode 1.

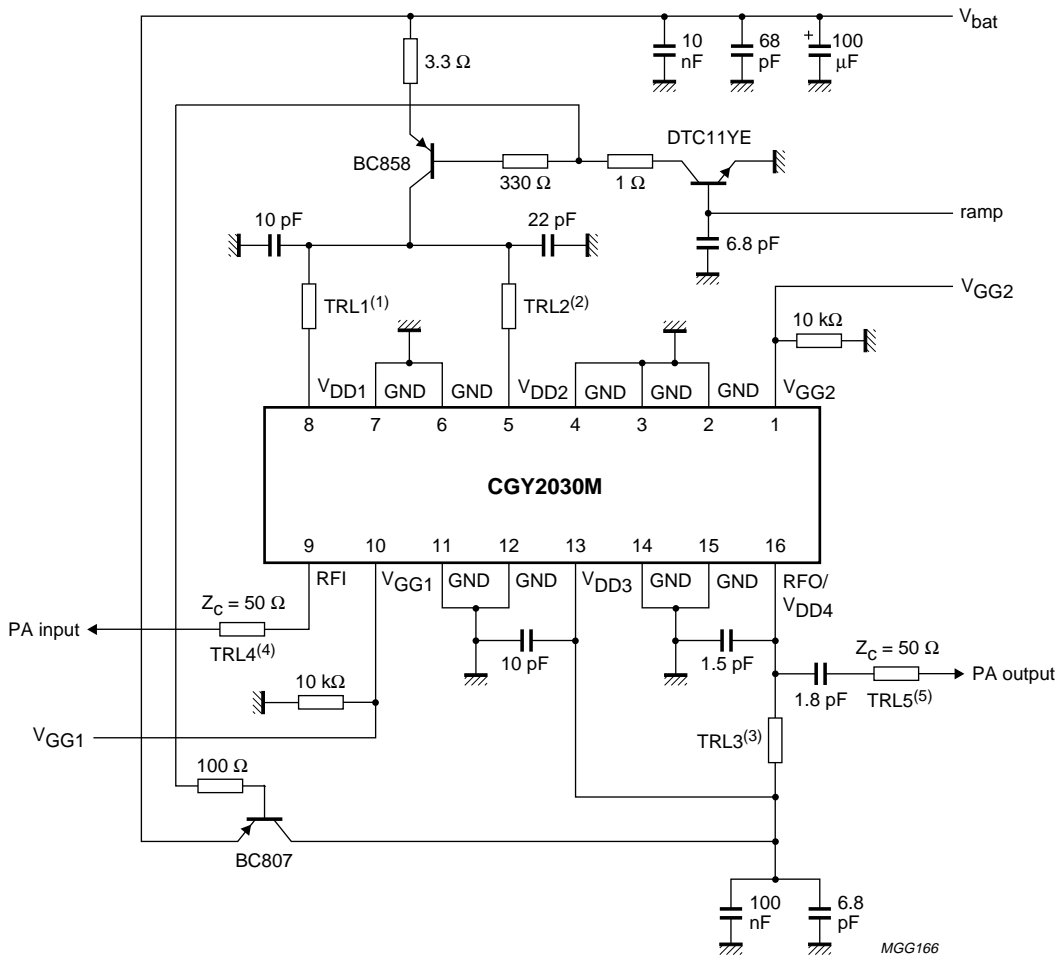
# DECT 500 mW power amplifier

# CGY2030M

### APPLICATION INFORMATION

The CGY2030M is operated and tested in accordance with the circuit diagram shown in Fig.4. Supply voltage switching is achieved by two bipolar PNP transistors. One transistor switches the first and second stages and the other switches the third and fourth stages.

By switching on the last amplifier stages with some delay compared to the first stages, it is possible to get the last stages already self-biased before their supply voltage has reached its steady state value. This enables smooth power up-ramping without any power overshoot. A simpler drain switching circuit can be used if the amplifier is operated with negative biasing of the pins  $V_{GG1}$  and  $V_{GG2}$ .



Thickness: 0.8 mm; substrate: FR4;  $\epsilon_r = 4.7$ .

- (1) TRL1: width = 500  $\mu\text{m}$ ; length = 11200  $\mu\text{m}$ .
- (2) TRL2: width = 500  $\mu\text{m}$ ; length = 7770  $\mu\text{m}$ .
- (3) TRL3: width = 300  $\mu\text{m}$ ; length = 15450  $\mu\text{m}$ .
- (4) TRL4: width = 1600  $\mu\text{m}$ ; length = 12000  $\mu\text{m}$ .
- (5) TRL5: width = 1600  $\mu\text{m}$ ; length = 11000  $\mu\text{m}$ .

Fig.4 Evaluation board schematic.

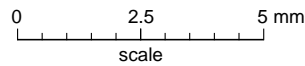
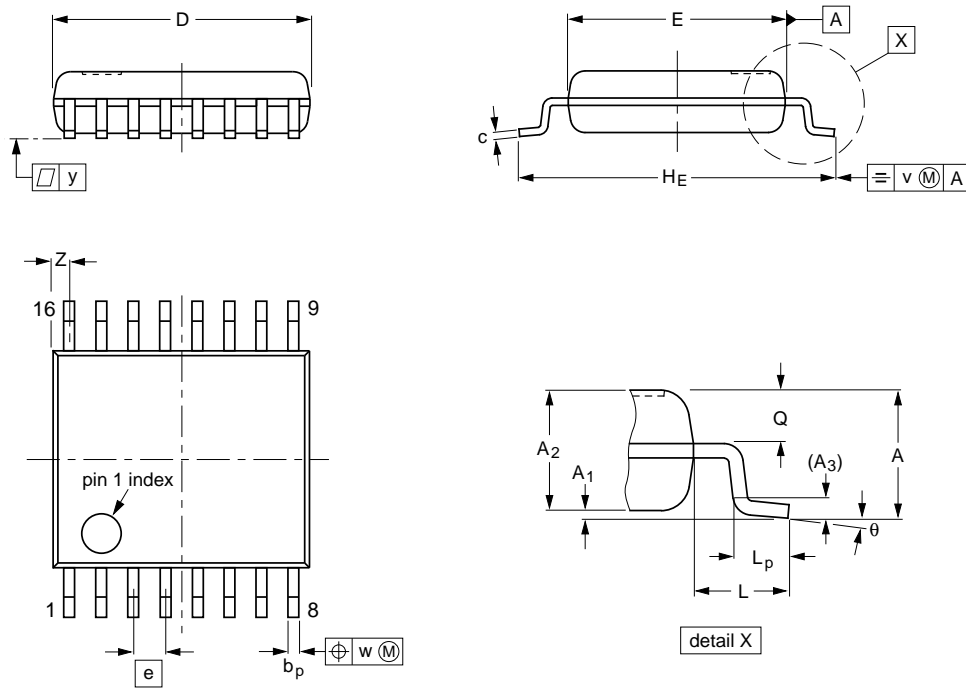
DECT 500 mW power amplifier

CGY2030M

PACKAGE OUTLINE

SSOP16: plastic shrink small outline package; 16 leads; body width 4.4 mm

SOT369-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b <sub>p</sub>	c	D <sup>(1)</sup>	E <sup>(1)</sup>	e	H <sub>E</sub>	L	L <sub>p</sub>	Q	v	w	y	Z <sup>(1)</sup>	θ
mm	1.5	0.15 0.00	1.4 1.2	0.25	0.32 0.20	0.25 0.13	5.30 5.10	4.5 4.3	0.65	6.6 6.2	1.0	0.75 0.45	0.65 0.45	0.2	0.13	0.1	0.48 0.18	10° 0°

Note

1. Plastic or metal protrusions of 0.20 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT369-1						94-04-20 95-02-04

---

## DECT 500 mW power amplifier

## CGY2030M

---

### SOLDERING

#### Introduction

There is no soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and surface mounted components are mixed on one printed-circuit board. However, wave soldering is not always suitable for surface mounted ICs, or for printed-circuits with high population densities. In these situations reflow soldering is often used.

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"IC Package Databook"* (order code 9398 652 90011).

#### Reflow soldering

Reflow soldering techniques are suitable for all SSOP packages.

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several techniques exist for reflowing; for example, thermal conduction by heated belt. Dwell times vary between 50 and 300 seconds depending on heating method. Typical reflow temperatures range from 215 to 250 °C.

Preheating is necessary to dry the paste and evaporate the binding agent. Preheating duration: 45 minutes at 45 °C.

#### Wave soldering

Wave soldering is **not** recommended for SSOP packages. This is because of the likelihood of solder bridging due to closely-spaced leads and the possibility of incomplete solder penetration in multi-lead devices.

If wave soldering cannot be avoided, the following conditions must be observed:

- **A double-wave (a turbulent wave with high upward pressure followed by a smooth laminar wave) soldering technique should be used.**
- **The longitudinal axis of the package footprint must be parallel to the solder flow and must incorporate solder thieves at the downstream end.**

**Even with these conditions, only consider wave soldering SSOP packages that have a body width of 4.4 mm, that is SSOP16 (SOT369-1) or SSOP20 (SOT266-1).**

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Maximum permissible solder temperature is 260 °C, and maximum duration of package immersion in solder is 10 seconds, if cooled to less than 150 °C within 6 seconds. Typical dwell time is 4 seconds at 250 °C.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

#### Repairing soldered joints

Fix the component by first soldering two diagonally-opposite end leads. Use only a low voltage soldering iron (less than 24 V) applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C. When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.



## DECT 500 mW power amplifier

CGY2030M

**DEFINITIONS**

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

**LIFE SUPPORT APPLICATIONS**

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

DECT 500 mW power amplifier

CGY2030M

---

**NOTES**

DECT 500 mW power amplifier

CGY2030M

---

**NOTES**

# Philips Semiconductors – a worldwide company

**Argentina:** see South America

**Australia:** 34 Waterloo Road, NORTH RYDE, NSW 2113,  
Tel. +61 2 9805 4455, Fax. +61 2 9805 4466

**Austria:** Computerstr. 6, A-1101 WIEN, P.O. Box 213,  
Tel. +43 1 60 101, Fax. +43 1 60 101 1210

**Belarus:** Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,  
220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773

**Belgium:** see The Netherlands

**Brazil:** see South America

**Bulgaria:** Philips Bulgaria Ltd., Energoproject, 15th floor,  
51 James Bourchier Blvd., 1407 SOFIA,  
Tel. +359 2 689 211, Fax. +359 2 689 102

**Canada:** PHILIPS SEMICONDUCTORS/COMPONENTS,  
Tel. +1 800 234 7381

**China/Hong Kong:** 501 Hong Kong Industrial Technology Centre,  
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,  
Tel. +852 2319 7888, Fax. +852 2319 7700

**Colombia:** see South America

**Czech Republic:** see Austria

**Denmark:** Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S,  
Tel. +45 32 88 2636, Fax. +45 31 57 1949

**Finland:** Sinikalliontie 3, FIN-02630 ESPOO,  
Tel. +358 9 615800, Fax. +358 9 61580/xxx

**France:** 4 Rue du Port-aux-Vins, BP317, 92156 SURESNES Cedex,  
Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427

**Germany:** Hammerbrookstraße 69, D-20097 HAMBURG,  
Tel. +49 40 23 53 60, Fax. +49 40 23 536 300

**Greece:** No. 15, 25th March Street, GR 17778 TAVROS/ATHENS,  
Tel. +30 1 4894 339/239, Fax. +30 1 4814 240

**Hungary:** see Austria

**India:** Philips INDIA Ltd, Shivsagar Estate, A Block, Dr. Annie Besant Rd.  
Worli, MUMBAI 400 018, Tel. +91 22 4938 541, Fax. +91 22 4938 722

**Indonesia:** see Singapore

**Ireland:** Newstead, Clonskeagh, DUBLIN 14,  
Tel. +353 1 7640 000, Fax. +353 1 7640 200

**Israel:** RAPAC Electronics, 7 Kehilat Saloniki St, TEL AVIV 61180,  
Tel. +972 3 645 0444, Fax. +972 3 649 1007

**Italy:** PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3,  
20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557

**Japan:** Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108,  
Tel. +81 3 3740 5130, Fax. +81 3 3740 5077

**Korea:** Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,  
Tel. +82 2 709 1412, Fax. +82 2 709 1415

**Malaysia:** No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,  
Tel. +60 3 750 5214, Fax. +60 3 757 4880

**Mexico:** 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,  
Tel. +9-5 800 234 7381

**Middle East:** see Italy

**Netherlands:** Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,  
Tel. +31 40 27 82785, Fax. +31 40 27 88399

**New Zealand:** 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,  
Tel. +64 9 849 4160, Fax. +64 9 849 7811

**Norway:** Box 1, Manglerud 0612, OSLO,  
Tel. +47 22 74 8000, Fax. +47 22 74 8341

**Philippines:** Philips Semiconductors Philippines Inc.,  
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,  
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

**Poland:** Ul. Lukiska 10, PL 04-123 WARSZAWA,  
Tel. +48 22 612 2831, Fax. +48 22 612 2327

**Portugal:** see Spain

**Romania:** see Italy

**Russia:** Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW,  
Tel. +7 095 755 6918, Fax. +7 095 755 6919

**Singapore:** Lorong 1, Toa Payoh, SINGAPORE 1231,  
Tel. +65 350 2538, Fax. +65 251 6500

**Slovakia:** see Austria

**Slovenia:** see Italy

**South Africa:** S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,  
2092 JOHANNESBURG, P.O. Box 7430 Johannesburg 2000,  
Tel. +27 11 470 5911, Fax. +27 11 470 5494

**South America:** Rua do Rocio 220, 5th floor, Suite 51,  
04552-903 São Paulo, SÃO PAULO - SP, Brazil,  
Tel. +55 11 821 2333, Fax. +55 11 829 1849

**Spain:** Balmes 22, 08007 BARCELONA,  
Tel. +34 3 301 6312, Fax. +34 3 301 4107

**Sweden:** Kottbygatan 7, Akalla, S-16485 STOCKHOLM,  
Tel. +46 8 632 2000, Fax. +46 8 632 2745

**Switzerland:** Allmendstrasse 140, CH-8027 ZÜRICH,  
Tel. +41 1 488 2686, Fax. +41 1 481 7730

**Taiwan:** Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1,  
TAIPEI, Taiwan Tel. +886 2 2134 2870, Fax. +886 2 2134 2874

**Thailand:** PHILIPS ELECTRONICS (THAILAND) Ltd.,  
209/2 Sanpavuth-Bangna Road Prakanong, BANGKOK 10260,  
Tel. +66 2 745 4090, Fax. +66 2 398 0793

**Turkey:** Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL,  
Tel. +90 212 279 2770, Fax. +90 212 282 6707

**Ukraine:** PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,  
252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

**United Kingdom:** Philips Semiconductors Ltd., 276 Bath Road, Hayes,  
MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421

**United States:** 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,  
Tel. +1 800 234 7381

**Uruguay:** see South America

**Vietnam:** see Singapore

**Yugoslavia:** PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD,  
Tel. +381 11 625 344, Fax. +381 11 635 777

**For all other countries apply to:** Philips Semiconductors, Marketing & Sales Communications,  
Building BE-p, P.O. Box 218, 5600 MD EINDHOVEN, The Netherlands, Fax. +31 40 27 24825

**Internet:** <http://www.semiconductors.philips.com>

© Philips Electronics N.V. 1997

SCA53

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands

437027/1200/03/pp12

Date of release: 1997 Jan 17

Document order number: 9397 750 01565

*Let's make things better.*

**Philips  
Semiconductors**



**PHILIPS**